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Docket No. 0756-2330

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )  
Shunpei YAMAZAKI et al. )  
Serial No. 09/894,125 )  
Filed: June 29, 2001 )  
For: CRYSTALLINE SEMICONDUCTOR )  
THIN FILM, METHOD OF FABRICATING )  
THE SAME, SEMICONDUCTOR DEVICE,)  
AND METHOD OF FABRICATING THE )  
SAME )

) Art Unit: 2823

) Examiner: B. Kebede

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Washington, D.C. 20231, on SEP 12 2002

Ava M. Dixon

**AMENDMENT**

Honorable Commissioner of Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated April 24, 2002 please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please amend claims 1-6, 10-12 and 19-30 as follows:

*D SUB* 1. (Amended) A method of manufacturing a semiconductor device comprising the steps of: forming a semiconductor film comprising silicon over a substrate; irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film; removing an oxide film formed on a surface of the semiconductor film by etching after the irradiation of the laser light; and leveling the surface of the semiconductor film by heating after removing said oxide film.

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